

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.154A	APPLICATION NO. 09/939,417
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Forbes	
		FILING DATE August 24, 2001	GROUP Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
KP	5,909,618	06/01/99	Forbes et al.				
KP	5,936,274	08/10/99	Forbes et al.				
KP	5,973,356	10/26/99	Noble et al.				
KP	5,991,225	11/23/99	Forbes et al.				
KP	6,072,209	06/06/00	Noble et al.				
KP	6,124,729	09/26/00	Noble et al.				
KP	6,134,175	10/17/00	Forbes et al.				
KP	6,143,636	11/07/00	Forbes et al.				
KP	6,150,687	11/21/00	Noble et al.				
KP	6,153,468	11/28/00	Forbes et al.				
KP	6,208,164	03/27/01	Noble et al.				

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	1.	Hergenrother et al., "The Vertical Replacement-Gate (VRG) MOSFET: A 50-nm Vertical MOSFET with Lithography-Independent Gate Length", Bell Laboratories, Lucent Technologies, NJ, USA, pages 1-4.

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EXAMINER	DATE CONSIDERED 04-19-02
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	